1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350Z

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- · High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- DC/DC converters
- · Supply line switching
- Battery charger
- LED backlighting
- Linear voltage regulation (LDO)
- Driver in low supply voltage applications, e.g. lamps, LEDs
- · Inductive load driver (for example relays, buzzers, motors)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	-50	V
Ic	collector current			-	-	-3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-5	Α
R _{CEsat}	collector-emitter saturation resistance	I _C = -2 A; I _B = -200 mA; T _{amb} = 25 °C	[1]	-	120	150	mΩ

[1] Pulsed test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$



50 V, 3 A PNP low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C
2	С	collector		В—
3	E	emitter		
4	С	collector	☐1 ☐2 ☐3 SC-73 (SOT223)	Ë sym132

6. Ordering information

Table 3. Ordering information

Type number Package					
	Name	Description	Version		
PBSS5350Z	SC-73	plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223		

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5350Z	PB5350

50 V, 3 A PNP low VCEsat (BISS) transistor

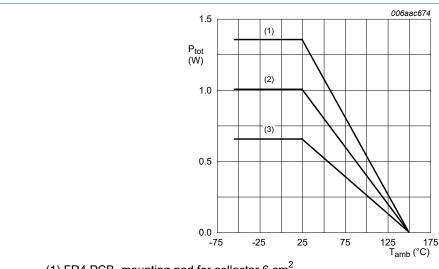
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-60	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-5	Α
I _{BM}	peak base current			-	-1	А
P _{tot}	total power dissipation		[1]	-	0.65	W
			[2]	-	1	W
			[3] [4]	-	1.35	W
			[5]	-	2	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), 35 µm single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 6 cm². [3]
- Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 1 cm² Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm² (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Power derating curves Fig. 1.

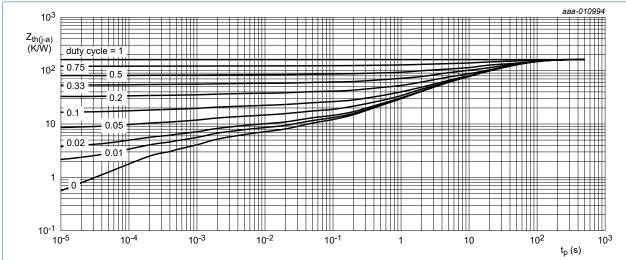
50 V, 3 A PNP low VCEsat (BISS) transistor

9. Thermal characteristics

Table 6. Thermal characteristics

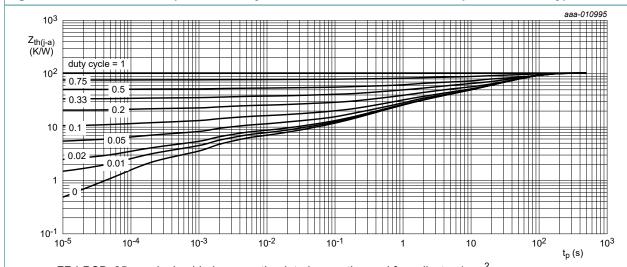
				_	_		_	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	192	K/W	
		junction to ambient		[2]	-	-	125	K/W
			[3] [4]	-	-	92	K/W	
			[5]	-	-	62.5	K/W	
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	16	K/W	

- Device mounted on an FR4 PCB, 35 μm single-sided copper, tin-plated and standard footprint.
- [2]
- Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 6 cm². Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 1 cm². [3]
- [4]
- Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 6 cm². [5]



FR4 PCB, 35 µm single-sided copper, tin-plated and standard footprint.

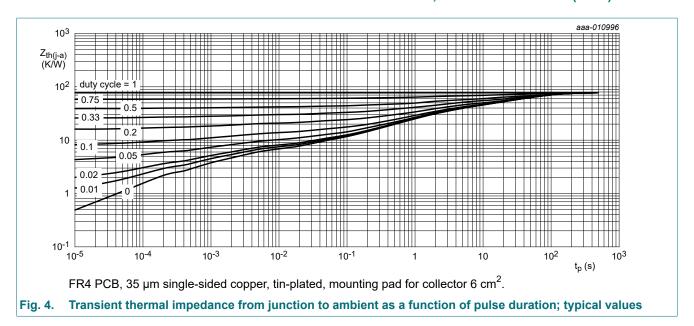
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 1 cm².

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	I _C = -100 μA; I _E = 0 A		-60	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}$		-50	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	I _E = -100 μA; I _C = 0 A		-6	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = -50 V; I _E = 0 A		-	-	-100	nA
	current	V _{CB} = -50 V; I _E = 0 A; T _j = 150 °C		-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A		-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -2 V; I _C = -500 mA		200	-	-	
		V _{CE} = -2 V; I _C = -1 A	[1]	200	-	-	
		V _{CE} = -2 V; I _C = -2 A	[1]	100	-	-	
V _{CEsat}	collector-emitter	I _C = -500 mA; I _B = -50 mA		-	-	-100	mV
saturation voltage	saturation voltage	I _C = -1 A; I _B = -50 mA		-	-	-180	mV
		I _C = -2 A; I _B = -200 mA	[1]	-	-	-300	mV
R _{CEsat}	collector-emitter saturation resistance	$I_C = -2 \text{ A}$; $I_B = -200 \text{ mA}$; $T_{amb} = 25 \text{ °C}$	[1]	-	120	150	mΩ
V_{BEsat}	base-emitter saturation voltage	I _C = -2 A; I _B = -200 mA	[1]	-	-	-1.2	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = -2 V; I _C = -1 A; T _{amb} = 25 °C	[1]	-	-	-1.1	V
f _T	transition frequency	V _{CE} = -5 V; I _C = -100 mA; f = 100 MHz		100	-	-	MHz

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz	-	-	40	pF

[1] Pulsed test: $t_p \le 300 \,\mu s$; $\delta \le 0.02$

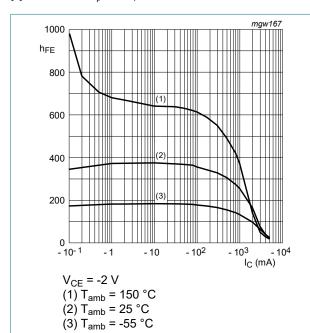


Fig. 5. DC current gain as a function of collector current; typical values

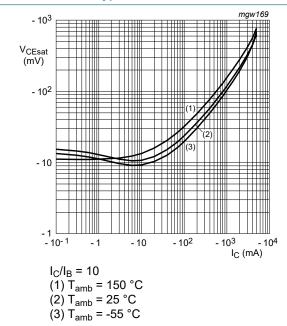


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

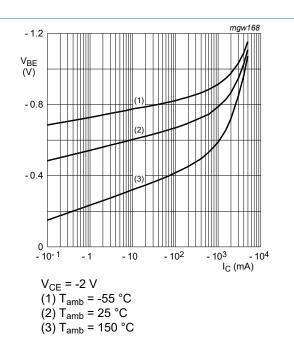


Fig. 6. Base-emitter voltage as a function of collector current; typical values

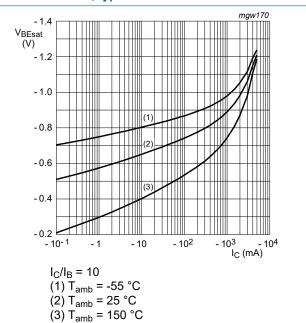
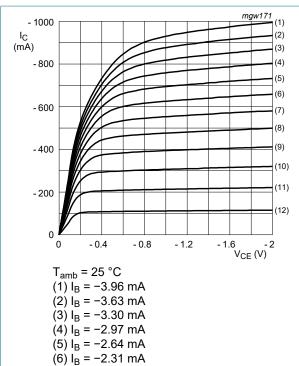


Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

50 V, 3 A PNP low VCEsat (BISS) transistor



 $(7) I_B = -1.98 \text{ mA}$ (8) $I_B = -1.65 \text{ mA}$

(9) $I_B = -1.32 \text{ mA}$

 $(10) I_B = -0.99 \text{ mA}$

 $(11) I_B = -0.66 \text{ mA}$

(12) $I_B = -0.33 \text{ mA}$

Fig. 9. Collector current as a function of collectoremitter voltage; typical values

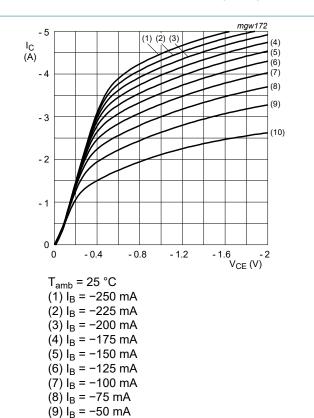
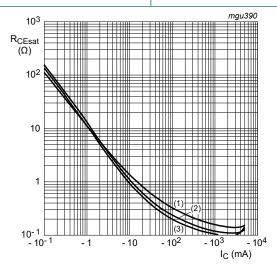


Fig. 10. Collector current as a function of collectoremitter voltage; typical values

(10) $I_B = -25 \text{ mA}$



 $I_C/I_B = 20$

 $(1) T_{amb} = 150 °C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55$ °C

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

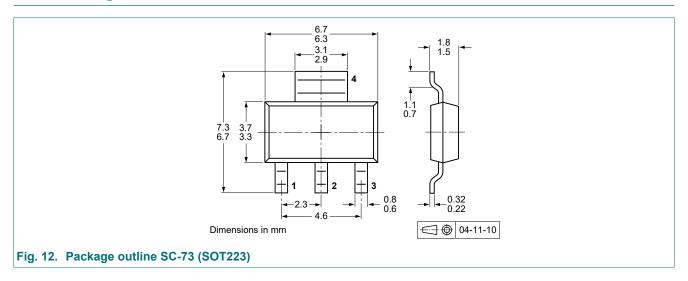
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11. Test information

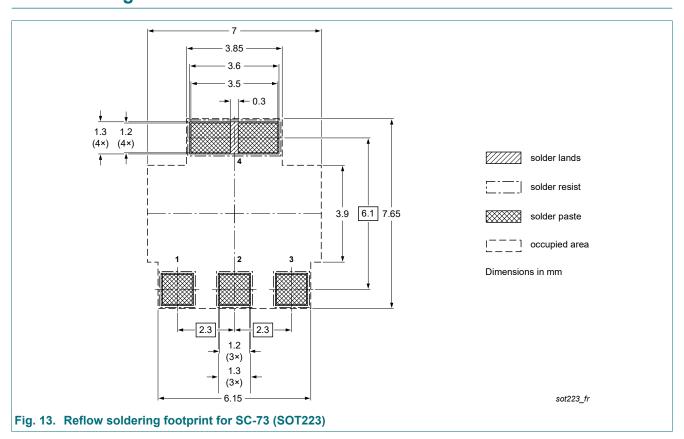
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

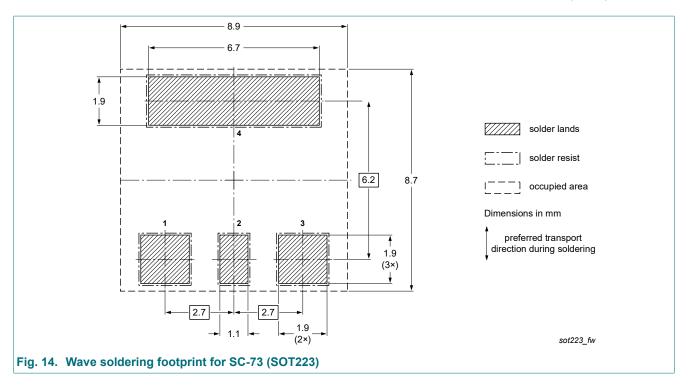
12. Package outline



13. Soldering



50 V, 3 A PNP low VCEsat (BISS) transistor



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14. Revision history

Table 8. Revision history

-	
Modifications: • The format of this data sheet has been redesigned to comply with the idea	upersedes
The format of this data sheet has been redesigned to comply with the iden	BSS5350Z v.4
 Legal texts have been adapted to the new company name where appropr 	, -
PBSS5350Z v.4 20030513 Product data sheet - PB	BSS5350Z v.3
PBSS5350Z v.3 20030120 Product data sheet - PB	BSS5350Z v.2
PBSS5350Z v.2 20011113 Product data sheet - PB	BSS5350Z v.1
PBSS5350Z v.1 20010717 Product data sheet	

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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